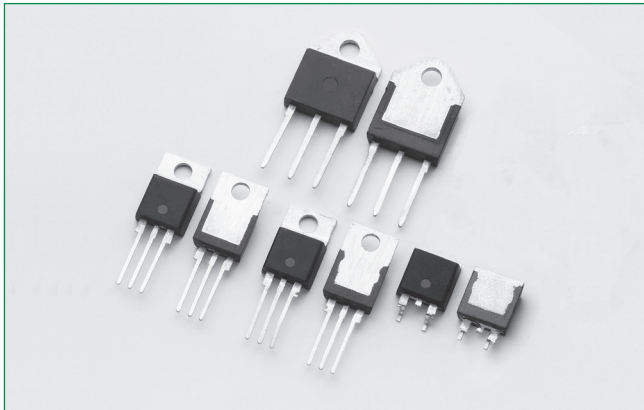


HQ6025xH5 Series



**Description**

The HQ6025xH5 is a 25 Amp bi-directional Alternistor Triac that is designed for AC switching and phase control applications that require a higher temperature environment. Alternistor type devices only operate in quadrants I, II, & are used in circuits requiring high dv/dt capability.

**Features & Benefits**

- 150°C maximum junction temperature
- RoHS-compliant
- Glass – passivated junctions
- Voltage capability up to 600 V
- Surge capability up to 300 A

**Agency Approval**

Agency	Agency File Number
	E71639*

\* - L and K Packages Only

**Applications**

Excellent for high-temperature environments applications where available heat-sinking is minimal such as heating and white goods.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

**Main Features**

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
$V_{DRM}/V_{RRM}$	600	V
$I_{GT}$	50	mA

**Additional Information**



Datasheet

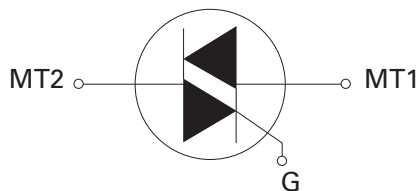


Resources



Samples

**Schematic Symbol**



### Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit	
$I_{T(RMS)}$	RMS on-state current	HQ6025LH5 $T_C = 95^\circ\text{C}$	25	A	
		HQ6025RH5 HQ6025NH5 HQ6025KH5 $T_C = 102^\circ\text{C}$			
$I_{TSM}$	Peak non-repetitive surge current	-	full cycle; $f = 50\text{Hz}$ ; $T_J$ (initial) = $25^\circ\text{C}$	250	A
			full cycle; $f = 60\text{Hz}$ ; $T_J$ (initial) = $25^\circ\text{C}$	300	
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3\text{ms}$	373	$\text{A}^2\text{s}$	
$di/dt$	Critical rate-of-rise of on-state current	$f = 60\text{Hz}; T_J = 150^\circ\text{C}$	100	$\text{A}/\mu\text{s}$	
$I_{GTM}$	Peak gate current	$T_J = 150^\circ\text{C}$	2	A	
$P_{G(AV)}$	Average gate power dissipation	$T_J = 150^\circ\text{C}$	0.5	W	
$T_{stg}$	Storage temperature range	-	-40 to 150	$^\circ\text{C}$	
$T_J$	Operating junction temperature range	-	-40 to 150	$^\circ\text{C}$	

### Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Test Conditions	Quadrant	Value	Unit	
$I_{GT}$	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III	MAX.	50	mA
$V_{GT}$	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III	MAX.	1.3	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_J = 150^\circ\text{C}$	I – II – III	MIN.	0.2	V
$I_H$	$I_T = 400\text{mA}$ (initial)		MAX.	80	mA
$dv/dt$	$V_D = V_{DRM}$ ; gate open; $T_J = 150^\circ\text{C}$		MIN.	350	$\text{V}/\mu\text{s}$
$(dv/dt)_c$	$(di/dt)_c = 13.3\ \text{A}/\text{ms}$ ; $T_J = 150^\circ\text{C}$		MIN.	20	$\text{V}/\mu\text{s}$
$t_{gt}$	$I_G = 2 \times I_{GT}$ $PW = 15\ \mu\text{s}$ $I_T = 35.4\text{A}$		TYP.	3	$\mu\text{s}$

### Static Characteristics

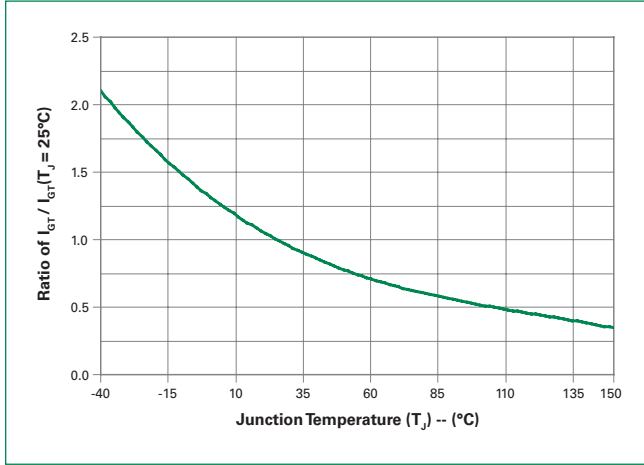
Symbol	Test Conditions	Value	Unit	
$V_{TM}$	$I_T = 35.4\text{A}$ ; $t_p = 380\ \mu\text{s}$	MAX.	1.4	V
$I_{DRM}/I_{RRM}$	$V_{DRM}/V_{RRM}$	$T_J = 25^\circ\text{C}$	5	$\mu\text{A}$
		$T_J = 150^\circ\text{C}$	6000	

### Thermal Resistances

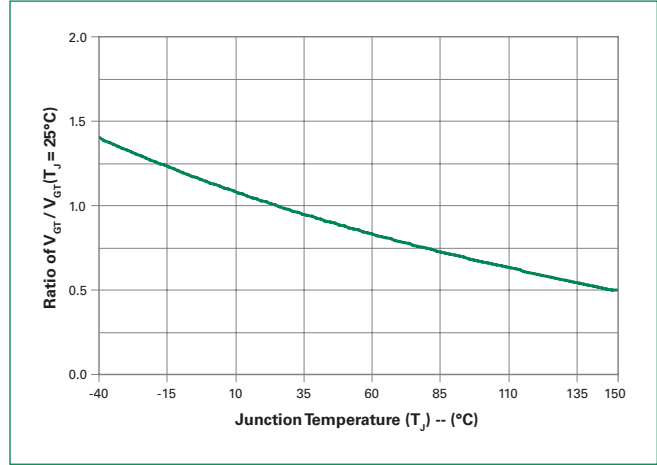
Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	HQ6025LH5	2.0
		HQ6025RH5 HQ6025NH5	0.86
		HQ6025KH5	1.35
$R_{\theta(J-A)}$	Junction to ambient	HQ6025LH5	50
		HQ6025RH5	45

Note: xx = voltage

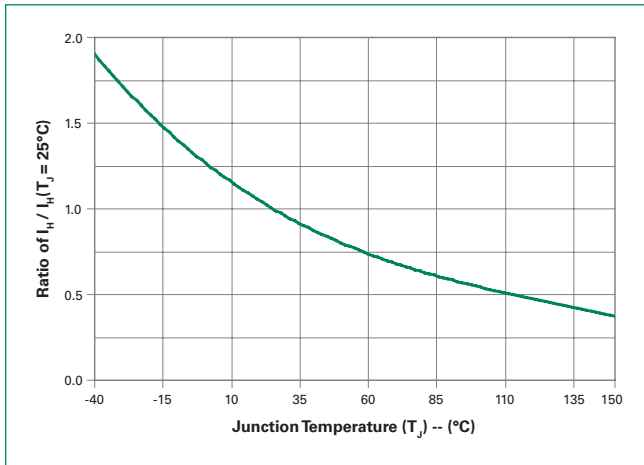
**Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature**



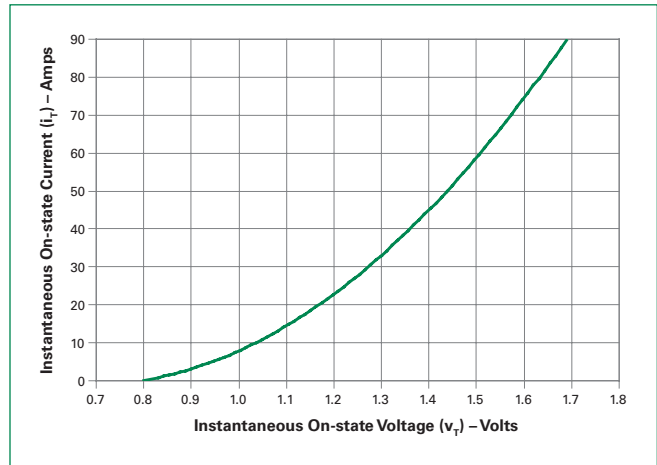
**Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature**



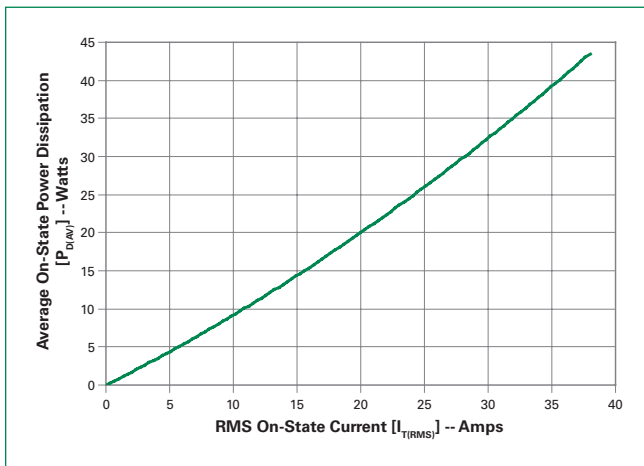
**Figure 3: Normalized DC Holding Current vs. Junction Temperature**



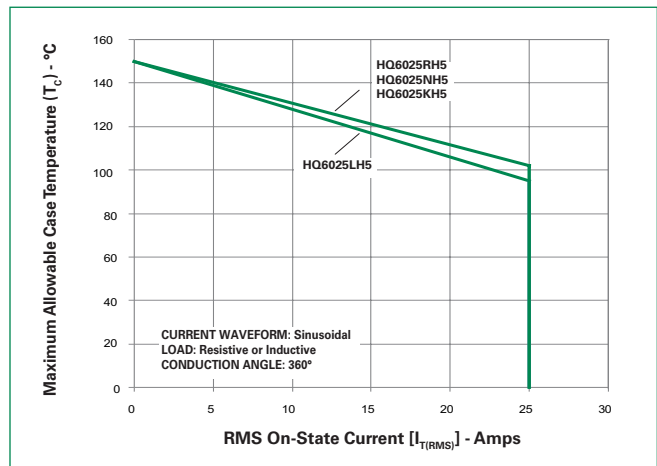
**Figure 4: On-State Current vs. On-State Voltage (Typical)**



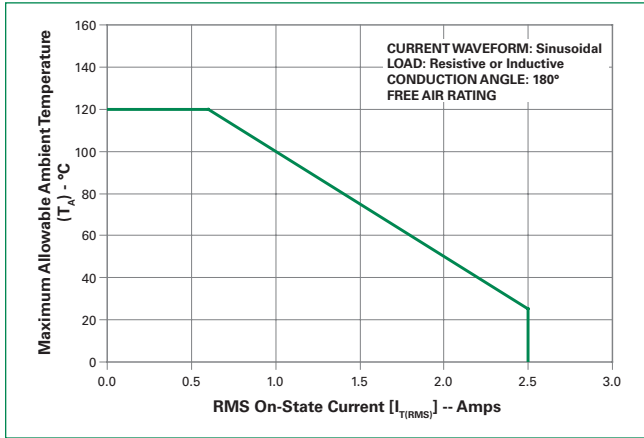
**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



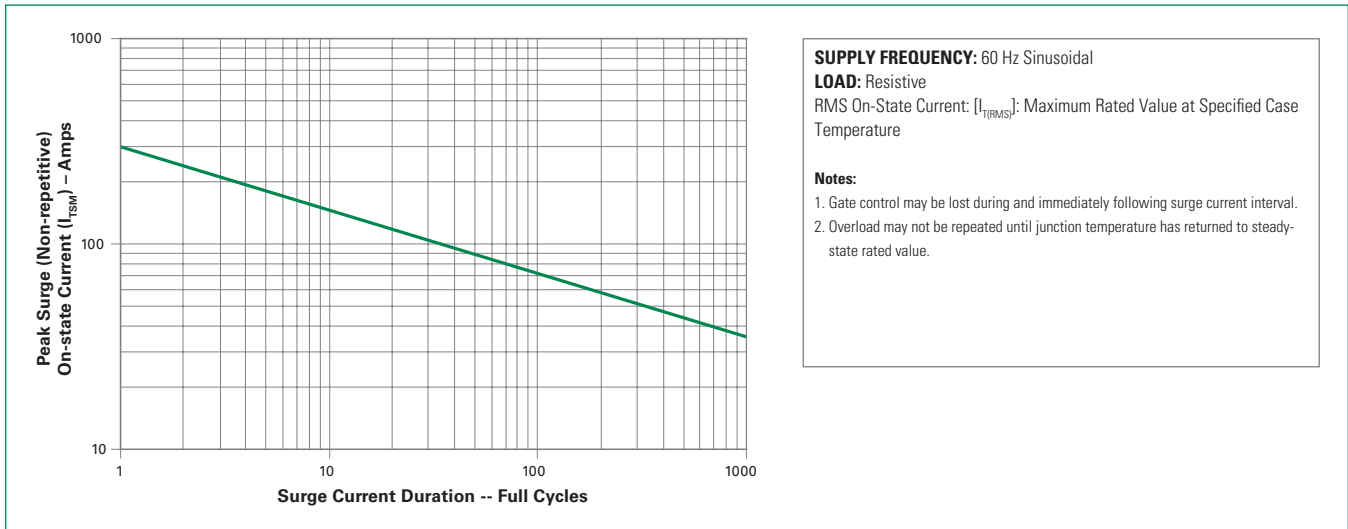
**Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current**



**Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current**

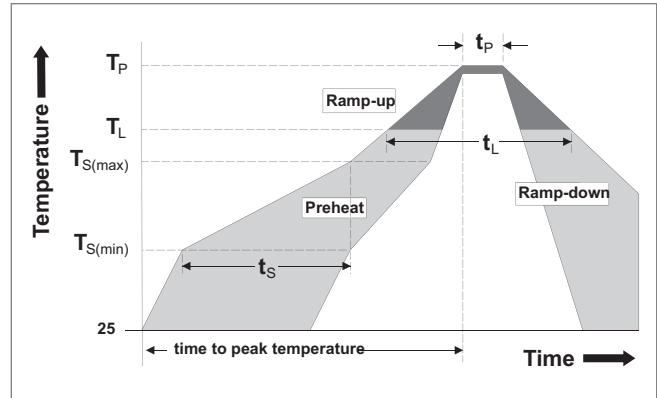


**Figure 8: Surge Peak On-State Current vs. Number of Cycles**



### Soldering Parameters

<b>Reflow Condition</b>		Pb – Free assembly
<b>Pre Heat</b>	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
<b>Average ramp up rate (Liquidus Temp) (<math>T_L</math>) to peak</b>		5°C/second max
<b><math>T_{s(max)}</math> to <math>T_L</math> - Ramp-up Rate</b>		5°C/second max
<b>Reflow</b>	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Temperature ( $t_L$ )	60 – 150 seconds
<b>Peak Temperature (<math>T_p</math>)</b>		260 <sup>+0/-5</sup> °C
<b>Time within 5°C of actual peak Temperature (<math>t_p</math>)</b>		20 – 40 seconds
<b>Ramp-down Rate</b>		5°C/second max
<b>Time 25°C to peak Temperature (<math>T_p</math>)</b>		8 minutes Max.
<b>Do not exceed</b>		280°C



### Physical Specifications

<b>Terminal Material</b>	Copper Alloy
<b>Terminal Finish</b>	100% Matte Tin Plated
<b>Body Material</b>	UL Recognized epoxy meeting flammability classification 94V-0

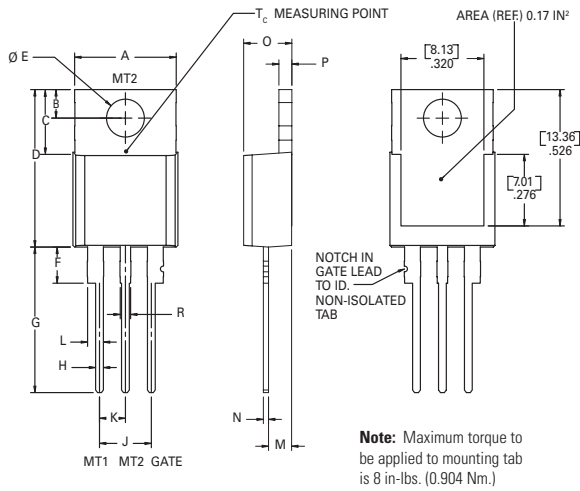
### Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including  $dv/dt$ ), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### Environmental Specifications

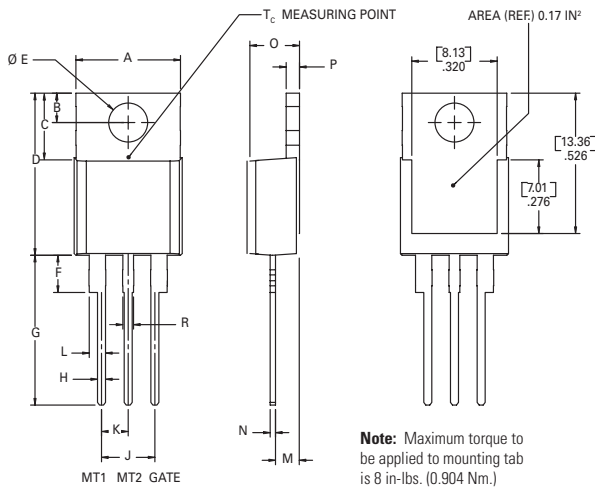
Test	Specifications and Conditions
<b>High Temperature Voltage Blocking</b>	MIL-STD-750: Method 1040, Condition A Rated $V_{RRM}$ : 150°C, 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750: Method 1051 -40°C to 150°C, 15-minute dwell, 100 cycles
<b>Biased Temp &amp; Humidity</b>	EIA/JEDEC: JESD22-A101 320VDC, 85°C, 85%RH, 1008 hours
<b>High Temp. Storage</b>	MIL-STD-750: Method 1031 150°C, 1008 hours
<b>Low-Temp Storage</b>	-40°C, 1008 hours
<b>Resistance to Solder Heat</b>	MIL-STD-750: Method 2031 260°C, 10 seconds
<b>Solderability</b>	ANSI/J-STD-002, Category 3, Test A
<b>Lead Bend</b>	MIL-STD-750: Method 2036, Condition E

**Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead**



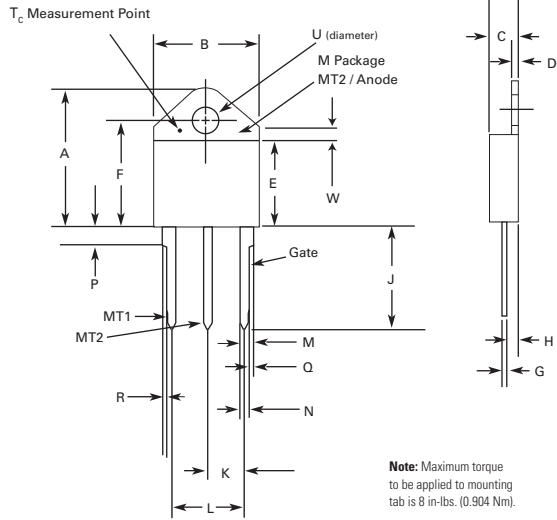
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

**Dimensions — TO-220AB (L Package) — Isolated Mounting Tab**



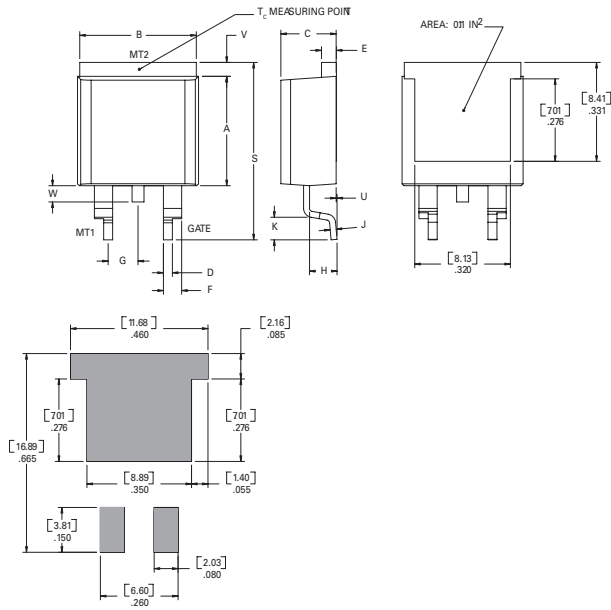
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

**Dimensions — TO-218AC (K Package) — Isolated Mounting Tab**



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.211	0.219	5.36	5.56
L	0.422	0.437	10.72	11.10
M	0.058	0.068	1.47	1.73
N	0.045	0.055	1.14	1.40
P	0.095	0.115	2.41	2.92
Q	0.008	0.016	0.20	0.41
R	0.008	0.016	0.20	0.41
U	0.159	0.163	4.04	4.14
W	0.085	0.095	2.17	2.42

**Dimensions — TO-263AB (N-Package) — D<sup>2</sup> -PAK Surface Mount**



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

**Product Selector**

Part Number	Voltage				Gate Sensitivity	Package
	400V	600V	800V	1000V		
HQ6025RH5	-	X	-	-	50 mA	TO-220R
HQ6025NH5	-	X	-	-	50 mA	TO-263
HQ6025LH5	-	X	-	-	50 mA	TO-220L
HQ6025KH5	-	X	-	-	50 mA	TO-218K